Si	gnature and Na	me of Invigilator	OMR Sheet No. :									
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	(Name)					(In f	igur	es as	per ac	dmiss	sion o	card)
2.	(Signature)				Roll No.							
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					Test Boo	okle	et N	Jo.				
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Ti	me : 1¼ hou	_					ſM	avin	111111	Mar	rks	: 100
		es in this Booklet : 16			Number of Q		-					
		ons for the Candidates			परीक्ष	-				200		
1.		imber in the space provided on the	top of	1.	पहले पृष्ठ के ऊपर नियत			•		लिखिए	1	
	this page.		-	2.	इस प्रश्न-पत्र में पचास बर्					•		
2.		s of fifty multiple-choice type of ques		3.	परीक्षा प्रारम्भ होने पर, प्रश							
3.		ment of examination, the question bo you. In the first 5 minutes, yo			आपको प्रश्न-पुस्तिका ख					बत जाँग	च के वि	लेए दिये
	requested to oper as below :	the booklet and compulsorily exan	nine it		जायेंगे जिसकी जाँच आप (i) प्रश्न-पुस्तिका खो						जगी ज	ਜਾਤ ਤੀ
	(i) To have acc	ess to the Question Booklet, tear o			 (i) प्रश्न-पुस्तिका खो सील को फाड़ लें 							
		on the edge of this cover page. D klet without sticker-seal and do not a			स्वीकार न करें।							
	an open boo		accpt		(ii) कवर पृष्ठ पर छपे							
		umber of pages and number of ques let with the information printed o			संख्या को अच्छी जिनमें पृष्ठ/प्रश्न							
	cover page.	Faulty booklets due to pages/ques	tions		अर्थात किसी भी	प्रकार	र की इ	, त्रुटिपूर्ण	पुस्तिक	त स्वीव	हार न व	करें तथा
		duplicate or not in serial order o pancy should be got replaced immed			उसी समय उसे लौ							
	by a correct booklet from the invigilator withi				ले लें। इसके लि तो आपकी प्रश्न							
		ninutes. Afterwards, neither the que l be replaced nor any extra time w			अतिरिक्त समय वि							
	given.	rification is even the Test Dealdet No			(iii) इस जाँच के बाद							
	should be	rification is over, the Test Booklet Nu entered in the OMR Sheet and	d the		अंकित करें और (अंकित कर दें।	JMR	(पत्रव	গ পগ সগ	મ સંख્યા	इस प्र	શ્ન-પુાર	स्तका पर
	OMR Sheet Booklet.	Number should be entered on this	s Test	4.	प्रत्येक प्रश्न के लिए चार	उत्तर वि	विकल	ч (А), ((B), (C)	तथा (]	D) दिये	ने गये हैं।
4.	Each item has fou	ır alternative responses marked (A		B), आपको सही उत्तर के दीर्घवृत्त को पेन से भरकर काला करना है जैसा							कि नीचे	
		u have to darken the oval as indi ect response against each item.	cated		दिखाया गया है।							
	Example : (A)	$(B) \bigoplus (D)$			उदाहरण : A (जबकि (C) सही उत्तर है।				D			
	where (C) is the c			5.	प्रश्नों के उत्तर केवल प्रश् न		के अ	न्दर दिर	ये गये उत्त	तर-पत्र	क पर हं	ो अंकित
5.	1	the items are to be indicated in the Ar			करने हैं। यदि आप उत्तर	पत्रक	पर वि	दये गये	दीर्घवृत्त	के अल	ावा कि	
		le the Paper I booklet only . If you t than in the ovals in the Answer Sh			स्थान पर उत्तर चिन्हांकित				मूल्यांकन्	न नहीं ह	होगा ।	
,	will not be evaluated	ated.		6. -				•	<u> </u>		`	
6. 7.		s given inside carefully. b be done in the end of this booklet		7. 8	कच्चा काम (Rough W यदि आप उत्तर-पुस्तिका प					-		
8.	If you write your	name or put any mark on any part	of the	0.	पहचान हो सके, किसी ध							
		pt for the space allotted for the rel y disclose your identity, you will re			लिये अयोग्य घोषित कर							
c	yourself liable to	disqualification.		9.	आपको परीक्षा समाप्त होने महोदय को लौटाना आवः							
9.		urn the test question booklet and o the invigilators at the end o			महादय का लोटाना आवर परीक्षा भवन से बाहर न ले			. _भ राषा	लनाति (ન બાહ	তল প	না লাপ
		pulsorily and must not carry it wit		10.	केवल नीले/काले बाल	ा प्वाई	ईंट पैन	। का ही	इस्तेमाल	न करें।		
10.		ack Ball point pen.		11.	किसी भी प्रकार का संग	गणक	(कै	लकुलेट	र) या	लाग टे	बल अ	गदि का
11.	Use of any calcul	ator or log table etc., is prohibited		10	प्रयोग वर्जित है।	_~~	<u> </u>					
12.	There is NO nega	ative marking.		12.	गलत उत्तर के लिए अंक	नहा र	काट	जायग।		_	_	
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ELECTRONIC SCIENCE PAPER – II

- **Note :** This paper contains **fifty** (50) objective-type questions, each question carrying **two** (2) marks. Attempt **all** of them.
- **1.** When the rms output voltage of the bridge full-wave rectifier is 20 V the PIV across the diode is :
 - (A) 28.2 (B) 19.3 (C) 40 (D) 31.42
- 2. When a Si transistor is in saturation mode the V_{CESAT} is :

(A) 5 V (B) 0.3 V (C) 1 V (D) 0 V

- **3.** For a two part reciprocal network, the output open-circuit voltage divided by the input current is equal to :
 - (A) B (B) Z_{12} (C) $\frac{1}{y_{12}}$ (D) h_{12}
- 4. The Laplace transform of (tsint) is :
 - (A) $\frac{2}{(s^2+1)^2}$ (B) $\frac{2s}{(s^2+1)^2}$
 - (C) $\frac{s}{(s^2+1)^2}$ (D) $\frac{2s}{(s^2-1)^2}$
- 5. For step input the output of an integrator is :
 - (A) a pulse (B) a triangular wave form
 - (C) a spike (D) a ramp

J - 8809

- 6. Two ideal FETs each characterized by the parameters g_m and r_d are connected in parallel. The composite FET is characterized by :
 - (A) $\frac{g_m}{2}$ and $2r_d$ (B) $\frac{g_m}{2}$ and $\frac{2r_d}{2}$
 - (C) $2g_m$ and $\frac{r_d}{2}$ (D) $2g_m$ and $2r_d$
- 7. A 3-Variable Karnaugh map has : (A) eight cells (B) three cells (C) sixteen cells (D) four cells The number of comparators in a parallel convertor type 8-bit A to D convertor : 8. (A) 8 (B) 16 (C) 256 (D) 255 9. The jump address of RST2 instruction in 8085 is : (A) 0000H (B) 0008H 0010H (D) 0018H (C) 10. Which I/O port of 8051 does not have dual function ? (B) P1 (C) P2 (A) P0 (D) P3 The FORTRAN statement $X = 5/10 + 3.0 \times 15/5.0 \times 2 + 10 \times 3$ will compute the value of 11. X as : (A) 48.5 (B) 48 (C) 34.5 (D) 35 12. Which conversion specifier is used with hexadecimal data type ? % f(A) % x(B) % d (C) (D) %*o*

J-8809

P.T.O.

- **13.** In a given medium $\frac{\sigma}{\omega\epsilon} = \sqrt{3}$. The magnetic and electric fields are out of phase by :
 - (A) 15° (B) 60° (C) 90° (D) 30°
- 14. A lossless line of length 500 m has $L=10 \ \mu$ H/m and $C=0.1 \ pF/m$ at 1 MHz. The electrical length of the line is :
 - (A) 360° (B) 270° (C) 180° (D) 90°
- **15.** If the carrier of a 100 percent modulated AM wave is suppressed, the percentage power saving will be :
 - (A) 50 (B) 66.66 (C) 150 (D) 100
- 16. Ten bit errors occur in two million transmitted bits. The bit error rate is :
 - (A) 2×10^{-5} (B) 5×10^{-5} (C) 5×10^{-6} (D) 2×10^{-6}

17. The value of ON - state voltage of an SCR is approximately :

- (A) 100 V (B) 50 V (C) 500 V (D) 2 V
- 18. A silicon photodetector cannot be used to detect the wavelength :
 - (A) $1.3 \ \mu m$ (B) $0.633 \ \mu m$ (C) $0.85 \ \mu m$ (D) $1.0 \ \mu m$
- 19. Which transducer has infinite resolution ?(A) thermistor (B) LVDT (C) thermocouple (D) RTD
- 20. Which controller produces residual error ?
 (A) On-off
 (B) Integral
 (C) Proportional
 (D) PID

Questions 21 to 30 : The following items consist of two statements, one labelled the "Assertion (A)" and the other labelled the "Reason (R)". You are to examine these two statements carefully and decide if the Assertion (A) and the Reason (R) are individually true and if so whether the Reason is a correct explanation of the Assertion. Select your answers to these items using the codes given below and mark your answer accordingly :

Codes :

- (A) Both (A) and (R) are true and (R) is the correct explanation of (A)
- (B) Both (A) and (R) are true but (R) in not correct explanation of (A)
- (C) (A) is true but (R) is false
- (D) (A) is false but (R) is true
- **21. Assertion (A) :** Silicon diodes are preferred to germanium diodes for high temperature operation.
 - **Reason (R) :** The reverse saturation current in a silicon diode is smaller than in a germanium diode.
- **22.** Assertion (A) : In two part networks Y and Z parameters are interrelated and hence need not be defined separately.
 - **Reason (R) :** Z parameters cannot be defined at high frequency but Y parameters can be defined.
- **23.** Assertion (A) : Multivibrators with 555 are preferred over those with BJT and digital ICs.
 - **Reason (R) :** 555 provides variation in duty cycle from 0 to 100% and drive a TTL load.
- 24. Assertion (A) : Race around condition occurs in all flip flops.Reason (R) : Race around condition occurs in logic circuits due to propagation delay.
- 25. Assertion (A) : Software interrupts are provided in 8086 microprocessors.

Reason (R) : Interrupts are generated by exceptions in 8086 microprocessors.

J – 8	8809
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- 26. Assertion (A) : Break statement is used in switch-case statement.
 - **Reason (R) :** In switch-case statement use of break prevents unrelated conditions to be skipped.
- **27.** Assertion (A) : An electromagnetic wave propagating in free space along the *z* direction is necessarily y polarized.
 - **Reason (R) :** Electromagnetic waves in free space are transverse waves.
- **28.** Assertion (A) : BPSK and QPSK modulation schemes increase the binary data rate in a given bandwidth.
 - **Reason (R) :** In QPSK modulation each pair of bits is represented by a specific phase.
- **29.** Assertion (A) : Modern optical communication systems use the 1.55 µm band.

Reason (R) : Pulse dispersion in optical fibers is minimum at $1.55 \mu m$.

- **30.** Assertion (A) : Thermistor linearity can be improved by connecting a resistor in series with the thermistor.
 - **Reason (R) :** Connecting a resistance in series with a thermistor will reduce the sensitivity.
- **31.** Consider the diodes given below.
 - (i) Germaniun diode
 - (ii) Silicon diode
 - (iii) Schottky diode
 - (iv) Point contact diode

The correct order of increasing cut-in voltage will be :

- (A) (iv) (i) (iii) (ii)
- (B) (i) (iii) (ii) (iv)
- (C) (ii) (iv) (iii) (i)
- (D) (iv) (ii) (i) (iii)

J – 8809

- **32.** Consider the following data size.
 - (i) Byte
 - (ii) Bit
 - (iii) Word
 - (iv) Nibble

The correct order of decreasing data size is :

(A) (ii) (i) (iii) (iv) (B) (iv) (iii) (ii) (i) (C) (iv) (i) (ii) (iii) (D) (iii) (i) (iv) (ii)

33. Consider the following guided transmission lines.

- (i) Coaxial cable
- (ii) Metallic waveguide
- (iii) Optical fiber
- (iv) Twisted pair

The correct order in increasing order of bandwidth is :

- (A) (iii) (ii) (i) (iv)
- (B) (ii) (i) (iii) (iv)
- (C) (iv) (i) (ii) (iii)
- (D) (iv) (ii) (iii) (i)

J-8809

- 34. Consider the following electromagnetic waves.
 - (i) Microwaves
 - (ii) X rays
 - (iii) Ultraviolet radiation
 - (iv) Infrared radiation

The correct order in increasing wave length is :

(A) (i) (iv) (iii) (ii) (B) (ii) (iii) (iv) (i) (C) (iii) (iv) (ii) (i) (D) (iv) (iii) (ii) (i)

35. Consider the following amplifier classes.

- (i) Class C
- (ii) Class A B
- (iii) Class A
- (iv) Class B

The correct order in increasing efficiencies is :

- (A) (ii) (iii) (iv) (i)
- (B) (iv) (iii) (iv) (i)
- (C) (iii) (iv) (ii) (i)
- (D) (iii) (ii) (iv) (i)

J – 8809

List-II

Isolation

Avalanche

Thermal runaway

Gate Capacitance

(a)	MOS	MOSFET									
(b)	Brea	Breakdown Diodes									
(c)	IC Fabrication (
(d)	Transistor										
Codes :											
	(a)	(b)	(c)	(<i>d</i>)							
(A)	(iii)	(iv)	(ii)	(i)							
(B)	(iv)	(ii)	(i)	(iii)							
(C)	(i) (ii) (iii) (iv)										

(D) (ii) (i) (iv) (iii)

List-I

37. Match the **List- I** with **List- II** and select the correct answer using the codes given below the lists :

	List-	-I		List-II						
(a)	Thev	renin's	s Theo	(i)	Transmission Line					
(b)	Poles	and	Zeroe	S	(ii)	Voltage Source				
(c)	Supe	erposit	tion T	heorem	(iii)	S - plane				
(d)	ABC	D Par	ramete	(iv)	Linear Network					
Code	Codes :									
	(a)	(b)	(c)	(<i>d</i>)						
(A)	(iv) (i) (iii) (ii)									
(B)	(i)	(ii)	(iii)	(iv)						
(C)	(ii)	(iii)	(iv)	(i)						

(i)

(D) (iii) (iv) (ii)

J — 8809

P.T.O.

	List-	-I					List-II
(a)	Diffe	erentia	ator			(i)	0.5 V / µs
(b)	Volta	age Re	egulat	or	(ii)	Wave shaping	
(c)	V to	F con	vertor		(iii)	IC 7809	
(d)	IC 74	41				(iv)	noise free transmission
Code	es :						
	(a)	(b)	(c)	(<i>d</i>)			
(A)	(iii)	(iv)	(ii)	(i)			
(B)	(ii)	(iii)	(iv)	(i)			
(C)	(iv)	(iii)	(i)	(ii)			
(D)	(iii)	(i)	(ii)	(iv)			

39. Match **List – I** with **List – II** and select the correct answer using the codes given below the lists :

	List	-I					List-II		
(a)	Cou	nters			(i)	Totempole output			
(b)	TTL	logic			(ii)	Sequential logic			
(c)	CMO)S			(iii)	Fastest logic			
(d)	ECL				(iv)	V _{DD} /3			
Codes :									
	(a)	(b)	(c)	(<i>d</i>)					
(A)	(i)	(ii)	(iii)	(iv)					
(B)	(iv)	(ii)	(iii)	(iv)					
(C)	(iii)	(i)	(iv)	(ii)					
(D)	(ii)	(i)	(iv)	(iii)					
						10			

J – 8809

10

List-I

List-II

- (A) IC 8279(b) IC 8251(c) Serial communication(c) Timer counter
- (C) IC 8051
- (D) IC 8155

(iii) Keyboard controller

(iv) Bit addressable RAM

Codes :

- (a) (b) (c) (d) (A) (i) (iii) (iv) (ii) (B) (iii) (iv) (ii) (i) (iii) (iv) (C) (ii) (i) (D) (iii) (iv) (i) (ii)
- **41.** Match **List I** with **List II** and select the correct answer using the codes given below the lists :

	List	List-I								
(a)	8 - 0	8 - Characters								
(b)	do -	do – while								
(c)	Com	Compiler and linker								
(d)	Stora	age cl	ass							
Code	es :									
	(a)	(b)	(c)	(<i>d</i>)						
(A)	(ii)	(iv)	(iii)	(i)						
(B)	(i) (iii) (iv) (ii)									
(C)	(iv) (ii) (i) (iii)									
(D)	(ii)	(i)	(iii)	(iv)						

J-8809

	List	-I					List-II				
(a)	Klys	tron			(i)	Negative Resistance					
(b)	Gun	n Dio	de		(ii)	Detection					
(c)	Mag	netro	n		(iii)	Bunching					
(d)	PIN	Diode	2		(iv)	Microwave Oven					
Cod	Codes :										
	(a)	(b)	(c)	(<i>d</i>)							
(A)	(i)	(ii)	(iv)	(iii)							
(B)	(i)	(iv)	(ii)	(iii)							
(C)	(iii)	(i)	(iv)	(ii)							
(D)	(iv)	(ii)	(i)	(ii)							

43. Match **List – I** with **List – II** and select the correct answer using the codes given below the lists :

	List-	-I				List-II
(a)	Amp	litude	e Mod	ulation	(i)	Frequency interleaving
(b)	Freq	uency	Mod	ulation	(ii)	Multiplexer
(c)	Time	e Divis	sion N	Iultiplexing	(iii)	Modulation index > 1
(d)	Freq	uency	Divis	ion Multiplexing	(iv)	Modulation index < 1
Code	?s :					
	(a)	(b)	(c)	(<i>d</i>)		
(A)	(iii)	(iv)	(ii)	(i)		
(B)	(iv) (iii) (i) (ii)					
(C)	(iii) (i) (ii) (iv)					
(D)	(iv)	(iii)	(ii)	(i)		

J — 8809

	List	- I			List-II						
(a)	Inter	rmoda	l Disp	persion	(i)	Photo diode					
(b)	Intra	amoda	al Disj	persion	(ii)	Laser					
(c)	Resp	onsiv	ity		(iii)	Multimode Fiber					
(d)	Qua	ntum	efficie	ency	(iv)	Single mode fiber					
Code	Codes :										
	(a)	(b)	(c)	(<i>d</i>)							
(A)	(iii)	(iv)	(ii)	(i)							
(B)	(iii) (iv) (i) (ii)										
(C)	(i)	(ii)	(iii)	(iv)							
(D)	(ii)	(iii)	(i)	(iv)							

45. Match **List – I** with **List – II** and select the correct answer using the codes given below the lists :

	List	-I					List-II			
(a)	Digi	tal Mı	ıltime	(i)	Phase					
(b)	Osci	llosco	pe	(ii)	Temperature					
(c)	Brid	ge		(iii)	4½ digit					
(d)	LM	35		(iv)	L or C					
Codes :										
	(a)	(b)	(c)	(<i>d</i>)						
(A)	(ii)	(iv)	(iii)	(i)						
(B)	(iii)	(iv)	(ii)	(i)						
(C)	(iii)	(i)	(iv)	(ii)						
(D)	(iv)	(iii)	(i)	(ii)						

J – 8809

P.T.O.

Read the passage below and answer the questions (46-50) that follow based on your understanding of the passage :

The tunnel diode is a thin junction diode which under low forward bias conditions exhibits negative resistance. Because of thin junction and short transit time, it lends to microwave application. Tunnel diode oscillators were found to be unstable. However, if a high Q cavity is loosely coupled to the diode, a highly stable oscillator is obtained with relative independence to temperature and bias voltage. The application of the tunnel diode was in microwave oscillations and negative resistance amplifier.

The diode voltage-current characteristics illustrate two important properties of the tunnel diode, namely, (i) diode exhibits dynamic negative resistance which is useful for oscillator and amplifier, (ii) negative resistance occurs when both the applied voltage and resulting current are low. The tunnel diode is a relatively low power device. The negative resistance is capable of significant power gain.

Tunnel diode amplifiers may be used through out the microwave range as moderate to low noise preamplifiers in all kinds of receivers. Tunnel diode amplifiers are immune to ambient radiation encountered in interplanetary space and hence, practicable for space work.

Gunn discovered the transferred electron effect and this effect was found in Gallium Arsenide and Indium Phosphide. Gunn diodes are used as low power oscillators in microwave receivers. The higher power Gunn oscillators are used as power output oscillators, which include police radars, CW Doppler radars and burglar alarms.

Gunn diodes are greatly superior to IMPATT diodes. Gunn diode amplifiers cannot compete for power output and low noise with GaAs FET amplifiers at frequencies below 30 GHz.

Step recovery diodes are junction diodes which can store energy in their capacitance and then generate harmonics by releasing a pulse of current. These diodes are widely employed in all microwave semiconductor devices. Such a diode is also called a snap – off varactor, which is a silicon or GaAs p-n junction diode. Step recovery diodes are used in amplifiers for low-level noise performance in the X – band

46. Indicate which of the following diodes does not use negative resistance for operation.

(A)	Schottky diode	(B)	Gunn diode
(C)	IMPATT	(D)	Tunnel diode

- 47. Which of the following is not used as a microwave detector ?
 - (A) Crystal diode (B) Schottky diode
 - (C) Backward diode (D) PIN diode

J - 8809

- 48. One of the following microwave diodes is suitable for low power oscillators only :
 - (A) Tunnel (B) Avalanche (C) Gunn (D) IMPATT

49. For best low level noise performance in the X-band one of the following should be used :

- (A) a bipolar transistor (B) a Gunn diode
- (C) a step recovery diode (D) an IMPATT diode
- 50. The transferred-electron bulk effect occurs in :
 - (A) Germanium (B) Gallium Arsenide
 - (C) Silicon (D) Metal Semiconductor Junction

-000-

Space For Rough Work